



T3

Peak pulse voltage ($T_j=25$; non-repetitive, off-state; FIG.8)	V_{pp}	1	kV
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(T_j=25 unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12V$ $R_L=33\Omega$	- -	MAX.	35	mA
V_{GT}		- -	MAX.	1.3	V
V_{GD}	$V_D=V_{DRM}$ $T_j=150$ $R_L=3.3k\Omega$	- -	MIN.	0.15	V
I_L	$I_G=1.2I_{GT}$	-	MAX.	70	mA
				80	
I_H	$I_T=500mA$		MAX.	50	mA
dV/dt	$V_D=540V$ Gate Open $T_j=150$		MIN.	1000	V/ μs
(dI/dt) _c	(dV/dt) _c =20V/ μs , $T_j=150$		MIN.	18	A/ms
t_{on}	$I_G=40mA$ $I_A=200mA$ $I_R=20mA$		TYP.	10	μs
t_{off}	$T_j=25$			80	

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	$I_{TM}=42A$ $t_p=380\mu s$	$T_j=25$	1.5	V
T_O	Threshold voltage	$T_j=150$	0.7	V
R_D	Dynamic resistance	$T_j=150$	16	m Ω
I_{DRM}	$V_D=V_{DRM}$ $V_R=V_{RRM}$	$T_j=25$	8	μA
I_{RRM}		$T_j=150$	8	mA

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	0.8	/W
$R_{th(j-a)}$	junction to ambient (AC, in free air, S=2cm ²)	45	/W

T 30 35 H -

FIG.1: Maximum power dissipation versus RMS on-state current

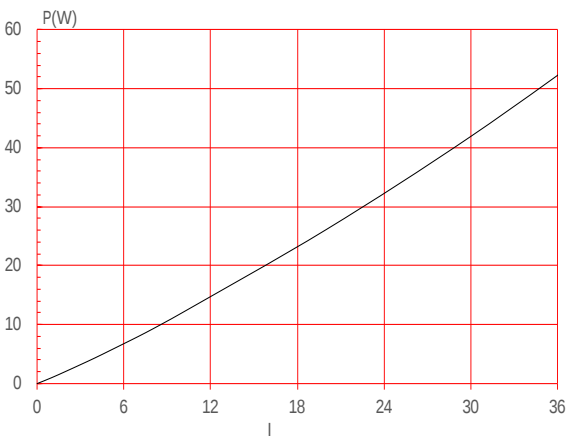
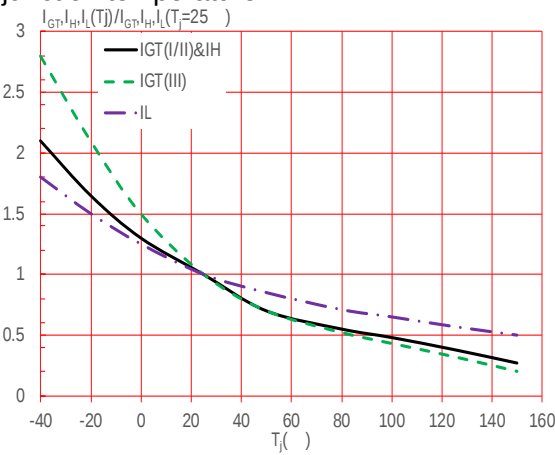
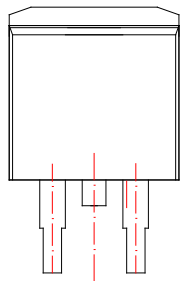


FIG.2: RMS on-state current versus case temperature
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FIG.7: Relative variations of gate trigger current, holding current and latching current versus junction temperature





Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	9.90		10.20	0.390		0.402
B	14.70		15.80	0.579		0.622
C	9.40		9.60	0.370		0.378
D	2.40			0.094		
E	1.20		1.50	0.047		0.059
F	0.75		0.85	0.029		0.033



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